

2N6674
2N6675

**NPN SILICON
POWER TRANSISTOR**



TO-3 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6674, 2N6675 types are NPN Silicon Triple Diffused Mesa Power Transistors designed for high voltage switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

Collector-Emitter Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Peak Collector Current
Continuous Base Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL	2N6674	2N6675	UNITS
V_{CEV}	450	650	V
V_{CEO}	300	400	V
V_{EBO}		7.0	V
I_C		15	A
I_{CM}		20	A
I_B		5.0	A
P_D		175	W
T_J, T_{stg}		-65 to +200	$^\circ\text{C}$
θ_{JC}		1.0	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEV}	$V_{CE}=\text{Rated } V_{CEV}, V_{BE}=1.5\text{V}$		0.1	mA
I_{CEV}	$V_{CE}=\text{Rated } V_{CEV}, V_{BE}=1.5\text{V}, T_C=100^\circ\text{C}$		1.0	mA
I_{EBO}	$V_{EB}=7.0\text{V}$		2.0	mA
BV_{CEO}	$I_C=200\text{mA}$ (2N6674)	300		V
BV_{CEO}	$I_C=200\text{mA}$ (2N6675)	400		V
$V_{CE(SAT)}$	$I_C=10\text{A}, I_B=2.0\text{A}$		1.0	V
$V_{CE(SAT)}$	$I_C=10\text{A}, I_B=2.0\text{A}, T_C=100^\circ\text{C}$		2.0	V
$V_{CE(SAT)}$	$I_C=15\text{A}, I_B=5.0\text{A}$		5.0	V
$V_{BE(SAT)}$	$I_C=10\text{A}, I_B=2.0\text{A}$		1.5	V
h_{FE}	$V_{CE}=2.0\text{V}, I_C=10\text{A}$	8.0	20	
$I_{S/b}$	$V_{CE}=30\text{V}, I_C=5.9\text{A}$	1.0		s
$I_{S/b}$	$V_{CE}=100\text{V}, I_C=250\text{mA}$	1.0		s
h_{fe}	$V_{CE}=10\text{V}, I_C=1.0\text{A}, f=5.0\text{MHz}$	3.0	10	
f_t	$V_{CE}=10\text{V}, I_C=1.0\text{A}, f=5.0\text{MHz}$	15	50	MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$	150	500	pF

R1 (10-March 2011)

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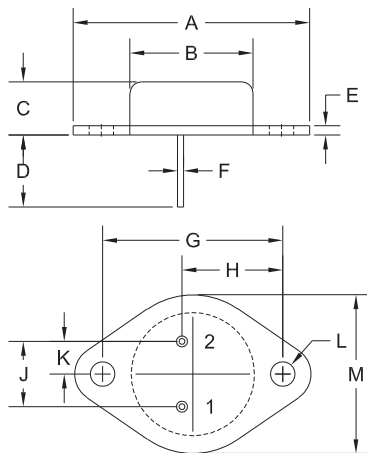


ELECTRICAL CHARACTERISTICS - Continued: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
t_d^*	$V_{EB}=6.0\text{V}, I_C=10\text{A}, I_B=2.0\text{A}$		0.1	μs
t_r^*	$V_{EB}=6.0\text{V}, I_C=10\text{A}, I_B=2.0\text{A}$		0.6	μs
t_f^*	$V_{EB}=6.0\text{V}, I_C=10\text{A}, I_B=2.0\text{A}, T_C=100^\circ\text{C}$		1.0	μs
t_s^*	$V_{EB}=6.0\text{V}, I_C=10\text{A}, I_{B1}=I_{B2}=2.0\text{A}$		2.5	μs
t_{S^*}	$V_{EB}=6.0\text{V}, I_C=10\text{A}, I_{B1}=I_{B2}=2.0\text{A}, T_C=100^\circ\text{C}$		4.0	μs
t_f^*	$V_{EB}=6.0\text{V}, I_C=10\text{A}, I_{B1}=I_{B2}=2.0\text{A}$		0.5	μs
t_{f^*}	$V_{EB}=6.0\text{V}, I_C=10\text{A}, I_{B1}=I_{B2}=2.0\text{A}, T_C=100^\circ\text{C}$		1.0	μs

* $V_{CC}=135\text{V}, t_p=20\mu\text{s}$

TO-3 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.516	1.573	38.50	39.96
B (DIA)	0.748	0.875	19.00	22.23
C	0.250	0.450	6.35	11.43
D	0.433	0.516	11.00	13.10
E	0.054	0.065	1.38	1.65
F	0.035	0.045	0.90	1.15
G	1.177	1.197	29.90	30.40
H	0.650	0.681	16.50	17.30
J	0.420	0.440	10.67	11.18
K	0.205	0.225	5.21	5.72
L (DIA)	0.151	0.172	3.84	4.36
M	0.984	1.050	25.00	26.67

TO-3 (REV: R2)

R2

LEAD CODE:

- 1) Base
- 2) Emitter
- Case) Collector

MARKING:

FULL PART NUMBER

R1 (10-March 2011)